

ABSTRACT OF THE DISCLOSURE

On a semiconductor substrate having a gate electrode and an LDD layer formed thereon, an SiN film to be a silicide block is formed. An opening communicating with the LDD layer is provided for the SiN film. Impurities are introduced into the LDD layer through the opening to form a source/drain layer, and the surface thereof is silicided to form a silicide film. Next, an interlayer insulation film of SiO<sub>2</sub> is formed and then etched under a condition of an etching rate of SiO<sub>2</sub> higher than that of SiN to form a contact hole reaching the LDD layer from the upper surface of the interlayer insulation film via the opening.